

[METHOD OF RELIEVING WAFER STRESS]

Abstract

A method of relieving wafer stress is provided. A wafer is provided, wherein at least a dielectric layer has already formed over the wafer and the wafer has a first and a second area. At least no circuits are formed on the dielectric layer within the first area. Thereafter, openings are formed in the dielectric layer within the first area. A material layer is formed over the dielectric layer. Thus, pits are formed on the surface of the material layer at locations above the openings. Through the pits on the material layer, stress within the material layer is relieved and hence the amount of stress conferred to the wafer is reduced.